

## Diode

Rapid Switching Emitter Controlled Diode

## IDW40E65D2

Emitter Controlled Diode

Data sheet

Industrial Power Control

## Rapid Switching Emitter Controlled Diode

### Features:

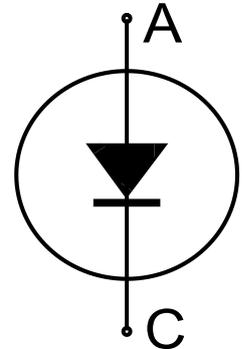
- Qualified according to JEDEC for target applications
- 650 V Emitter Controlled technology
- Fast recovery
- Soft switching
- Low reverse recovery charge
- Low forward voltage and stable over temperature
- 175 °C junction operating temperature
- Easy paralleling
- Pb-free lead plating; RoHS compliant

### Applications:

- Boost diode in CCM PFC

### Package pin definition:

- Pin 1 - not connected
- Pin 2 - cathode
- Pin 3 - anode



### Key Performance and Package Parameters

Type	$V_{rrm}$	$I_f$	$V_f, T_{vj}=25^{\circ}\text{C}$	$T_{vjmax}$	Marking	Package
IDW40E65D2	650V	40A	1.6V	175°C	E40ED2	PG-TO247-3



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## Emitter Controlled Diode

**Maximum Ratings**

For optimum lifetime and reliability, Infineon recommends operating conditions that do not exceed 80% of the maximum ratings stated in this datasheet.

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RRM}$	650	V
Diode forward current, limited by $T_{vjmax}$ $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_F$	80.0 40.0	A
Diode pulsed current, $t_p$ limited by $T_{vjmax}$	$I_{Fpuls}$	120.0	A
Diode surge non repetitive forward current $T_C = 25^\circ\text{C}$ , $t_p = 8.3\text{ms}$ , sine halfwave	$I_{FSM}$	250.0	A
Power dissipation $T_C = 25^\circ\text{C}$	$P_{tot}$	180.0	W
Operating junction temperature	$T_{vj}$	-40...+175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s		260	$^\circ\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	$M$	0.6	Nm

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
Diode thermal resistance, <sup>1)</sup> junction - case	$R_{th(j-c)}$		0.84	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		40	K/W

**Electrical Characteristic, at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Diode forward voltage	$V_F$	$I_F = 40.0\text{A}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	- -	1.60 1.65	2.30 -	V
Reverse leakage current	$I_R$	$V_R = 650\text{V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	- -	- -	40.0 4000.0	$\mu\text{A}$

**Electrical Characteristic, at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Dynamic Characteristic</b>						
Internal emitter inductance measured 5mm (0.197 in.) from case	$L_E$		-	13.0	-	nH

<sup>1)</sup> Please be aware that in non standard load conditions, due to high  $R_{th(j-c)}$ ,  $T_{vj}$  close to  $T_{vjmax}$  can be reached.

## Emitter Controlled Diode

## Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

 Diode Characteristic, at  $T_{vj} = 25^{\circ}\text{C}$ 

Diode reverse recovery time	$t_{rr}$	$T_{vj} = 25^{\circ}\text{C}$ , $V_R = 400\text{V}$ , $I_F = 40.0\text{A}$ , $di_F/dt = 1000\text{A}/\mu\text{s}$	-	36	-	ns
Diode reverse recovery charge	$Q_{rr}$		-	0.40	-	$\mu\text{C}$
Diode peak reverse recovery current	$I_{rrm}$		-	22.0	-	A
Diode peak rate of fall of reverse recovery current during $t_b$	$di_{rr}/dt$		-	-10000	-	$\text{A}/\mu\text{s}$
Diode reverse recovery time	$t_{rr}$	$T_{vj} = 25^{\circ}\text{C}$ , $V_R = 400\text{V}$ , $I_F = 40.0\text{A}$ , $di_F/dt = 200\text{A}/\mu\text{s}$	-	75	-	ns
Diode reverse recovery charge	$Q_{rr}$		-	0.13	-	$\mu\text{C}$
Diode peak reverse recovery current	$I_{rrm}$		-	2.9	-	A
Diode peak rate of fall of reverse recovery current during $t_b$	$di_{rr}/dt$		-	-54	-	$\text{A}/\mu\text{s}$

## Switching Characteristic, Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	

 Diode Characteristic, at  $T_{vj} = 175^{\circ}\text{C}/125^{\circ}\text{C}$ 

Diode reverse recovery time	$t_{rr}$	$T_{vj} = 175^{\circ}\text{C}$ , $V_R = 400\text{V}$ , $I_F = 40.0\text{A}$ , $di_F/dt = 1000\text{A}/\mu\text{s}$	-	60	-	ns
Diode reverse recovery charge	$Q_{rr}$		-	1.14	-	$\mu\text{C}$
Diode peak reverse recovery current	$I_{rrm}$		-	32.0	-	A
Diode peak rate of fall of reverse recovery current during $t_b$	$di_{rr}/dt$		-	-8700	-	$\text{A}/\mu\text{s}$
Diode reverse recovery time	$t_{rr}$	$T_{vj} = 125^{\circ}\text{C}$ , $V_R = 400\text{V}$ , $I_F = 40.0\text{A}$ , $di_F/dt = 200\text{A}/\mu\text{s}$	-	83	-	ns
Diode reverse recovery charge	$Q_{rr}$		-	0.32	-	$\mu\text{C}$
Diode peak reverse recovery current	$I_{rrm}$		-	5.6	-	A
Diode peak rate of fall of reverse recovery current during $t_b$	$di_{rr}/dt$		-	-51	-	$\text{A}/\mu\text{s}$

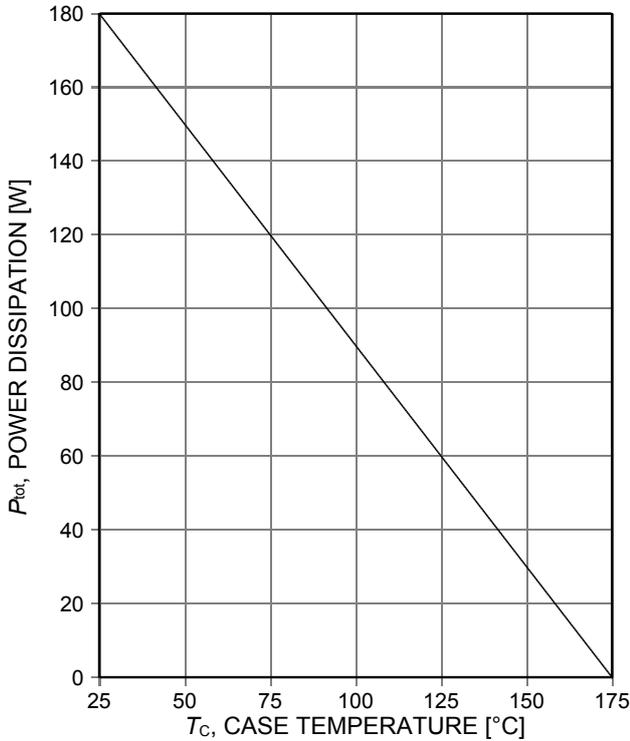


Figure 1. Power dissipation as a function of case temperature ( $T_{vj} \leq 175^\circ\text{C}$ )

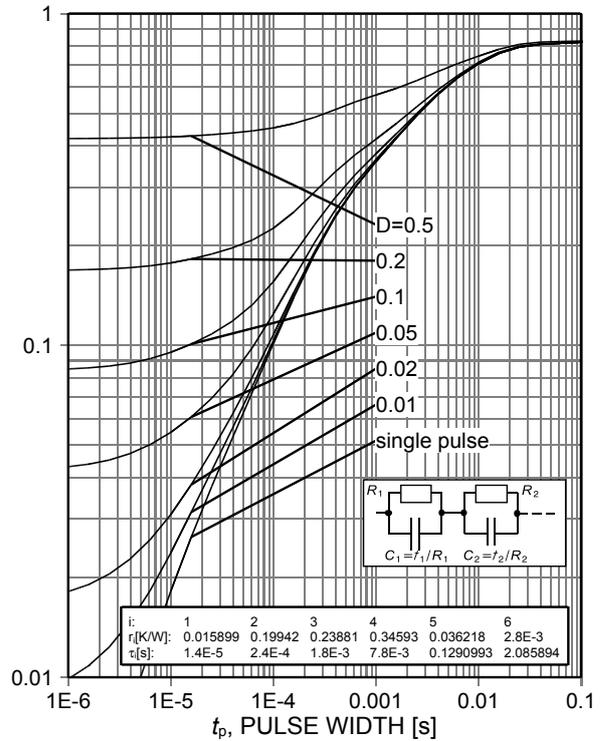


Figure 2. Diode transient thermal impedance as a function of pulse width ( $D = t_p/T$ )

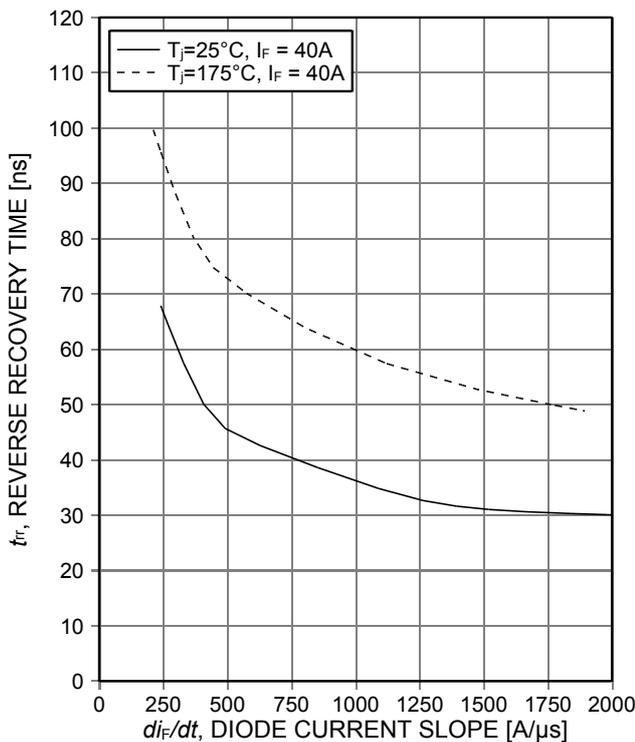


Figure 3. Typical reverse recovery time as a function of diode current slope ( $V_R=400\text{V}$ )

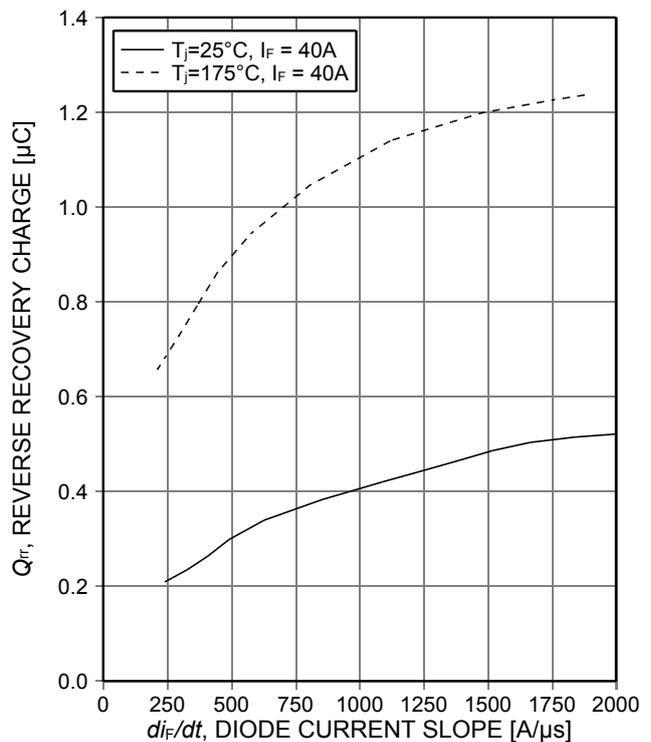


Figure 4. Typical reverse recovery charge as a function of diode current slope ( $V_R=400\text{V}$ )

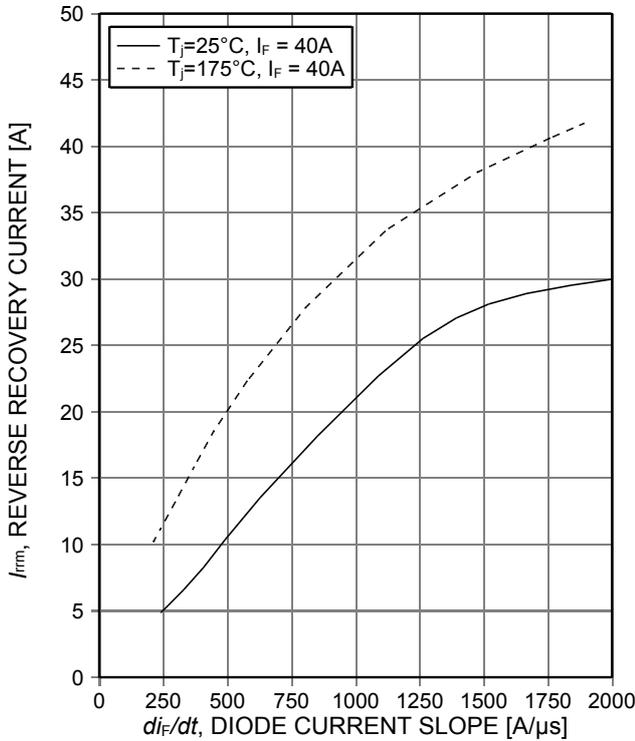


Figure 5. Typical peak reverse recovery current as a function of diode current slope ( $V_R=400V$ )

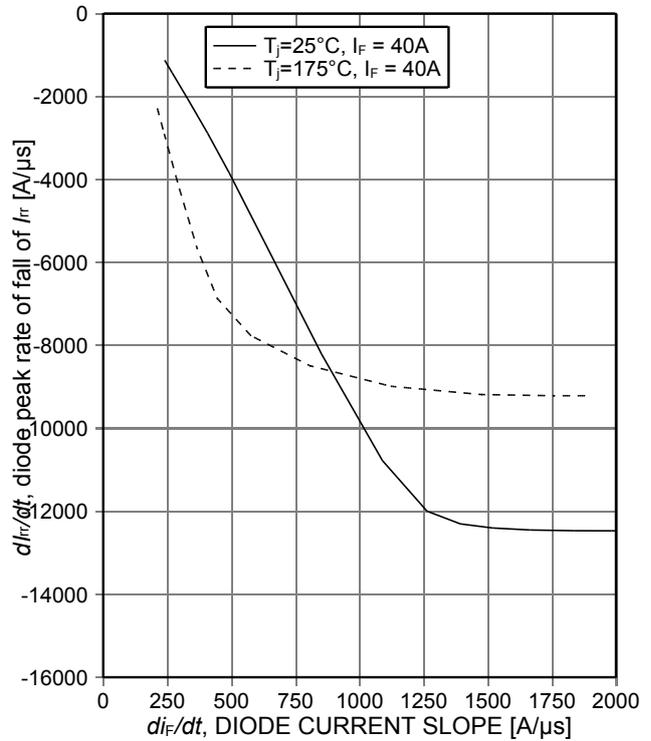


Figure 6. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope ( $V_R=400V$ )

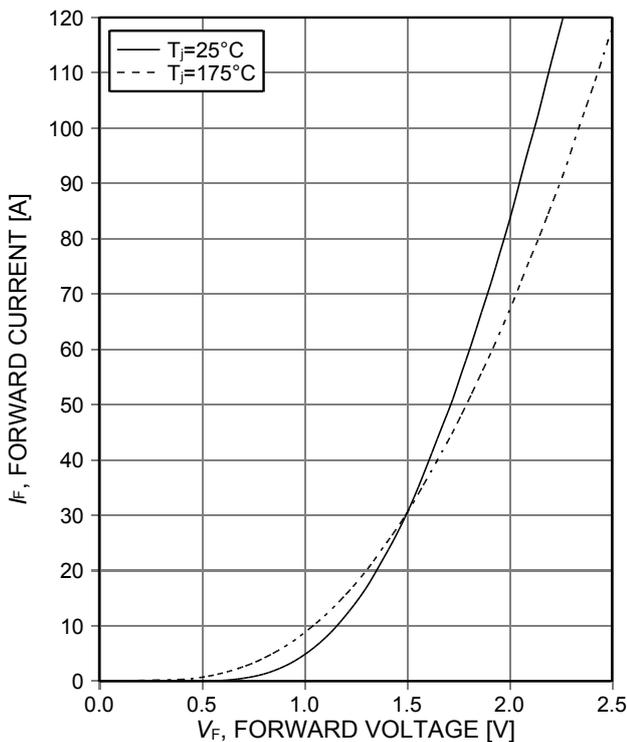


Figure 7. Typical diode forward current as a function of forward voltage

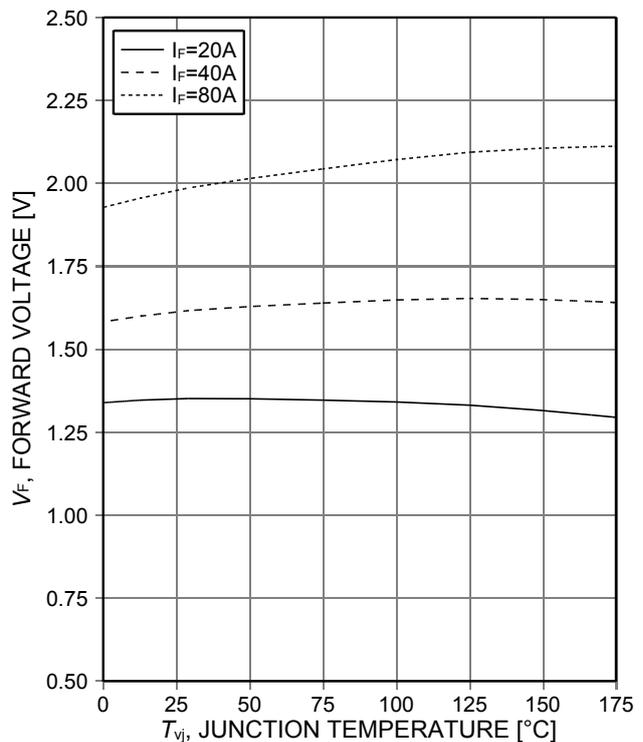
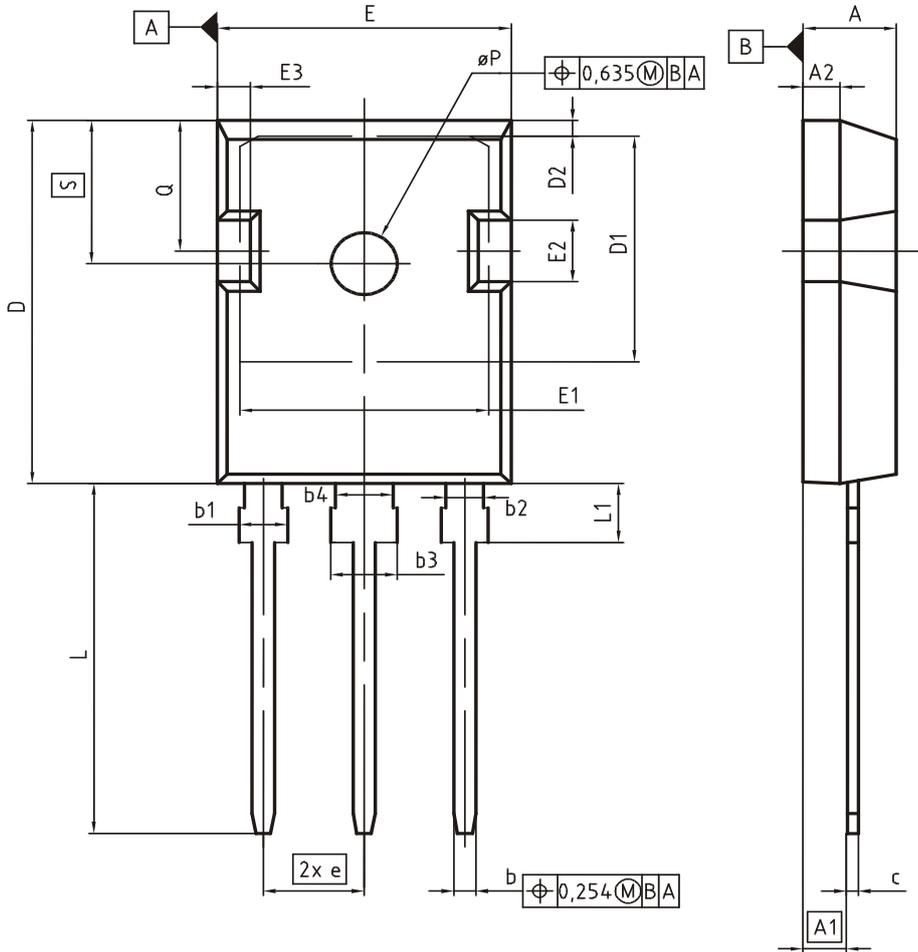


Figure 8. Typical diode forward voltage as a function of junction temperature

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
øP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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SCALE  
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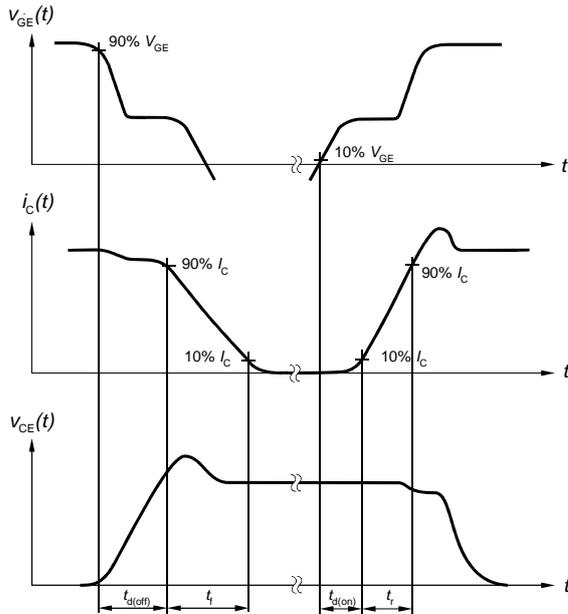


Figure A. Definition of switching times

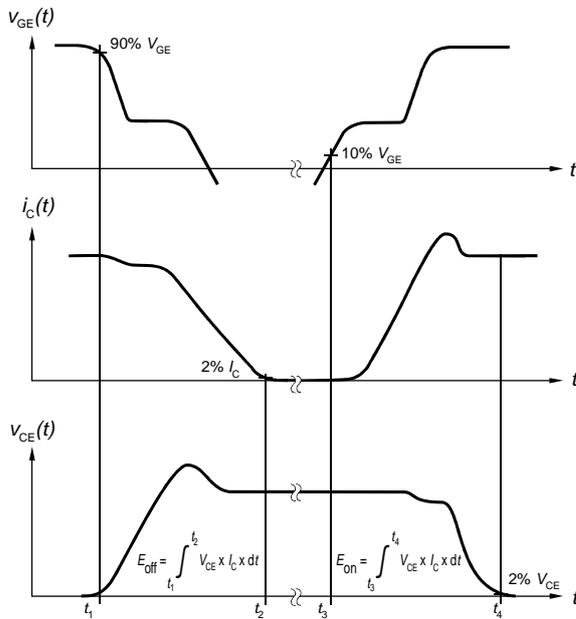


Figure B. Definition of switching losses

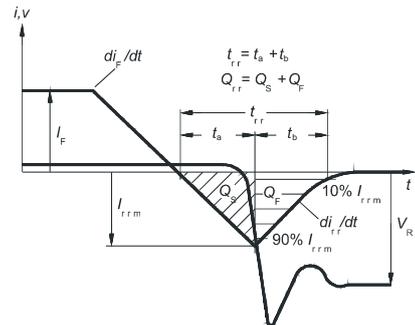


Figure C. Definition of diodes switching characteristics

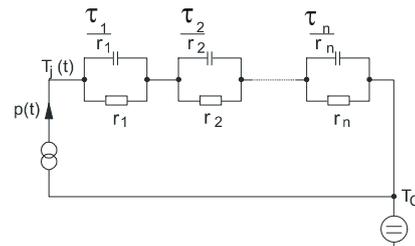


Figure D. Thermal equivalent circuit

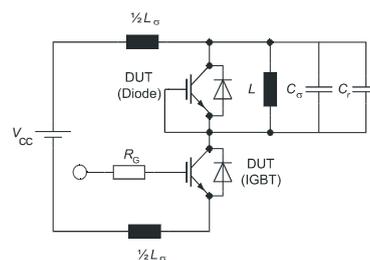


Figure E. Dynamic test circuit  
Parasitic inductance  $L_\sigma$ ,  
Parasitic capacitor  $C_\sigma$ ,  
Relief capacitor  $C_r$   
(only for ZVT switching)

## Revision History

IDW40E65D2

Revision: 2013-12-16, Rev. 2.1

## Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.1	2013-03-14	Preliminary data sheet
1.2	2013-05-22	I <sub>FSM</sub>
2.1	2013-12-16	Final DS / New Marking Pattern
2.2	2013-12-16	Value VF <sub>max</sub> limit according BE test

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